



ELECTRONICS, INC.
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NTE5693/NTE5695/NTE5697 NTE56022/NTE56024/NTE56026 TRIAC, 40 Amp

Description:

This NTE 40 Amp series medium power TRIACs are bi-directional triode thyristors which may be switched from off-state to conduction for either polarity of applied voltage with positive or negative gate triggering. These devices are designed for control of AC loads in applications such as lighting, heating and motor speed control, as well as static switching relays. These devices are available in a standard TO48 package (NTE5693, NTE5695, and NTE5697) or an Isolated TO48 package (NTE56022, NTE56024, and NTE56026).

Absolute Maximum Ratings:

Repetitive Peak Off-State Voltage ($T_J = +100^\circ\text{C}$), V_{DRM}

NTE5693, NTE56022	200V
NTE5695, NTE56024	400V
NTE5697, NTE56026	600V

Repetitive Peak Reverse Voltage ($T_J = +100^\circ\text{C}$), V_{RRM}

NTE5693, NTE56022	200V
NTE5695, NTE56024	400V
NTE5697, NTE56026	600V

RMS On-State Current ($T_C = +75^\circ\text{C}$, 360° Continuous), $I_{T(RMS)}$ 40A

Peak Surge (Non-Repetitive) On-State Current, I_{TSM}

One-Cycle, 60Hz	400A
One-Cycle, 50Hz	350A

Peak Gate-Trigger Current ($3\mu\text{s}$ Max), I_{GTM} 12A

Peak Gate-Power Dissipation ($I_{GT} \leq I_{GTM}$ for $3\mu\text{s}$ Max), P_{GM} 40W

Average Gate-Power Dissipation, $P_{G(AV)}$ 750mW

Operating Junction Temperature Range, T_{opr} -40° to $+100^\circ\text{C}$

NTE56026 ONLY -65° to $+110^\circ\text{C}$

Storage Temperature Range, T_{stg} -40° to $+150^\circ\text{C}$

NTE56026 ONLY -65° to $+150^\circ\text{C}$

Thermal Resistance, Junction-to-Case, R_{thJC}

NTE5693, NTE5695, NTE5697	1.8°C/W
NTE56022, NTE56024	2.1°C/W
NTE56026	1°C/W



Electrical Characteristics: (At Maximum Ratings and Indicated Case Temperatures unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Peak Off-State Current	I_{DROM}	$T_J = +100^{\circ}\text{C}$, Gate Open, $V_{DROM} = \text{Max Rating}$	–	–	4	mA
Maximum On-State Voltage	V_T	$T_C = +25^{\circ}\text{C}$, $I_T = 100\text{A}$ (Peak)	–	–	2	V
DC Holding Current	I_{HOLD}	$T_C = +25^{\circ}\text{C}$, Gate Open	–	–	60	mA
Critical rate-of-Rise of Off-State Voltage NTE5693, NTE56022	Critical dv/dt	$T_C = +100^{\circ}\text{C}$, At V_{DROM} , Gate Open	–	200	–	V/ μs
NTE5695, NTE56024			–	150	–	V/ μs
NTE5697, NTE56026			–	100	–	V/ μs
Critical Rate-of-Rise of Commutation Voltage	Commutating dv/dt	$T_C = +75^{\circ}\text{C}$, Gate Unenergized, $V_D = V_{DROM}$, $T = I_{T(RMS)}$, Commutating di/dt = 16A/ms	3	–	–	V/ μs
DC Gate-Trigger Current (T_2+ , Gate+; T_2- , Gate–) Quads I–II	I_{GT}	$T_C = +25^{\circ}\text{C}$, $V_D = 12\text{VDC}$, $R_L = 30\Omega$	–	–	50	mA
(T_2+ , Gate–; T_2- , Gate+) Quads II–IV			–	–	80	mA
DC Gate-Trigger Voltage	V_{GT}	$T_C = +25^{\circ}\text{C}$, $V_D = 12\text{VDC}$, $R_L = 30\Omega$	–	–	2.5	V
Gate-Controlled Turn-On Time	t_{gt}	$T_C = +25^{\circ}\text{C}$, $V_D = V_{DROM}$, $I_{GT} = 300\text{mA}$, $t_r = 0.1\mu\text{s}$, $I_T = 10\text{A}_{(Peak)}$	–	3	–	μs

